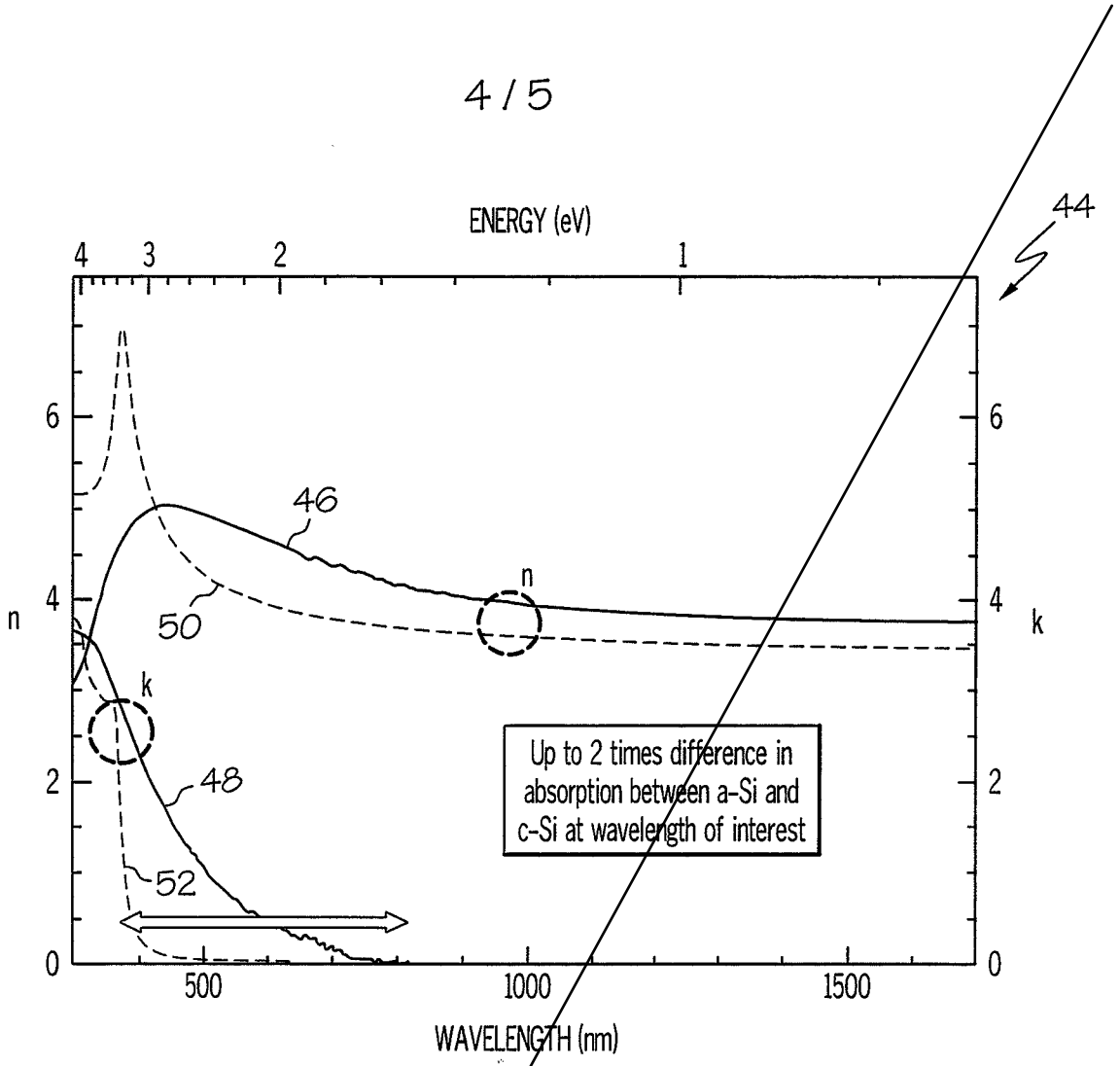

ENERGY (eV)
4
3
2
1
44
6
4
2
0
n
k
46
50
48
52
n
k
Up to 2 times difference in absorption between a-Si and c-Si at wavelength of interest
500
1000
1500
WAVELENGTH (nm)

FIG. 7

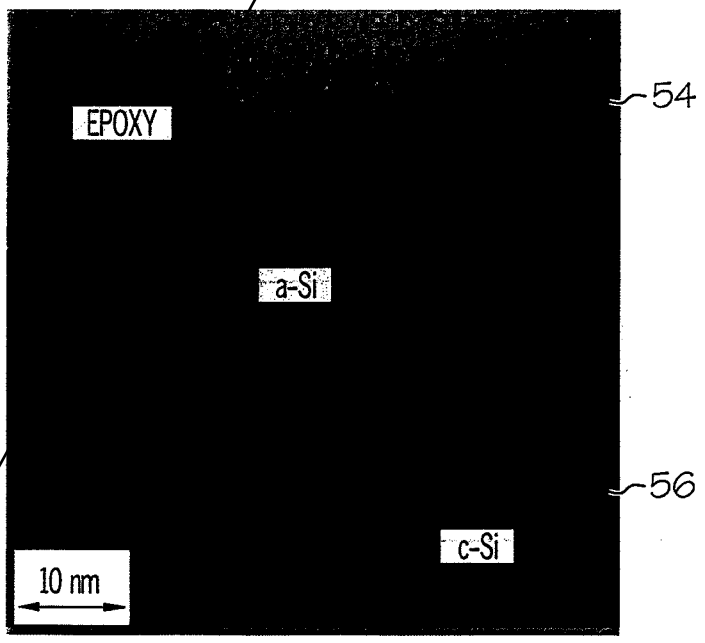

EPOXY
54
a-Si
56
c-Si
10 nm

FIG. 8

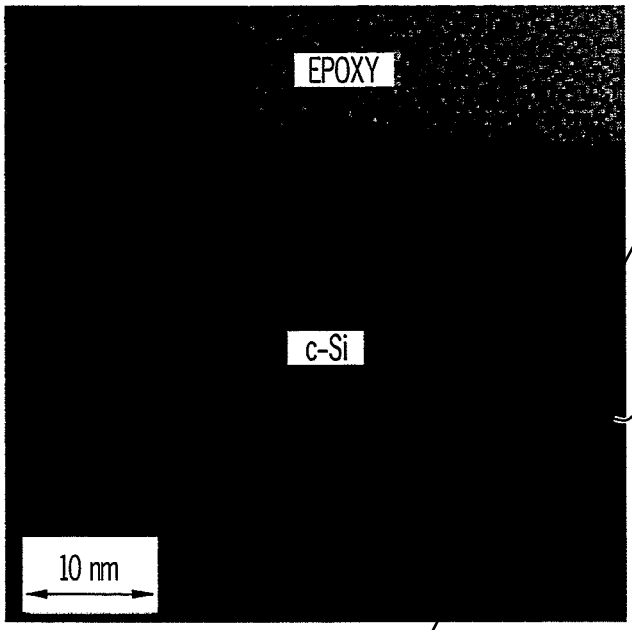

EPOXY
c-Si
10 nm
58

FIG. 9

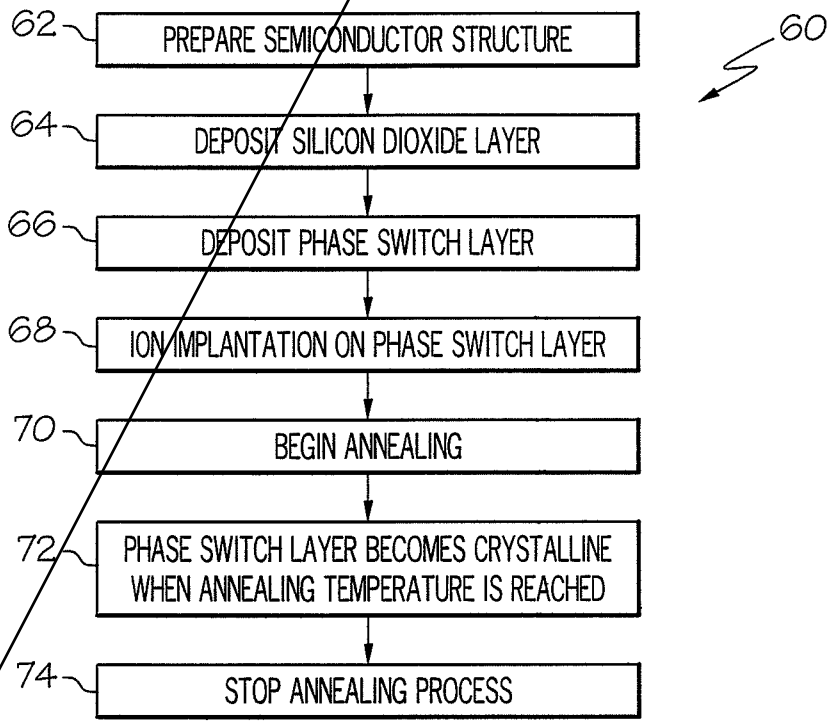

62
PREPARE SEMICONDUCTOR STRUCTURE
64
DEPOSIT SILICON DIOXIDE LAYER
66
DEPOSIT PHASE SWITCH LAYER
68
ION IMPLANTATION ON PHASE SWITCH LAYER
70
BEGIN ANNEALING
72
PHASE SWITCH LAYER BECOMES CRYSTALLINE WHEN ANNEALING TEMPERATURE IS REACHED
74
STOP ANNEALING PROCESS
60

FIG. 10

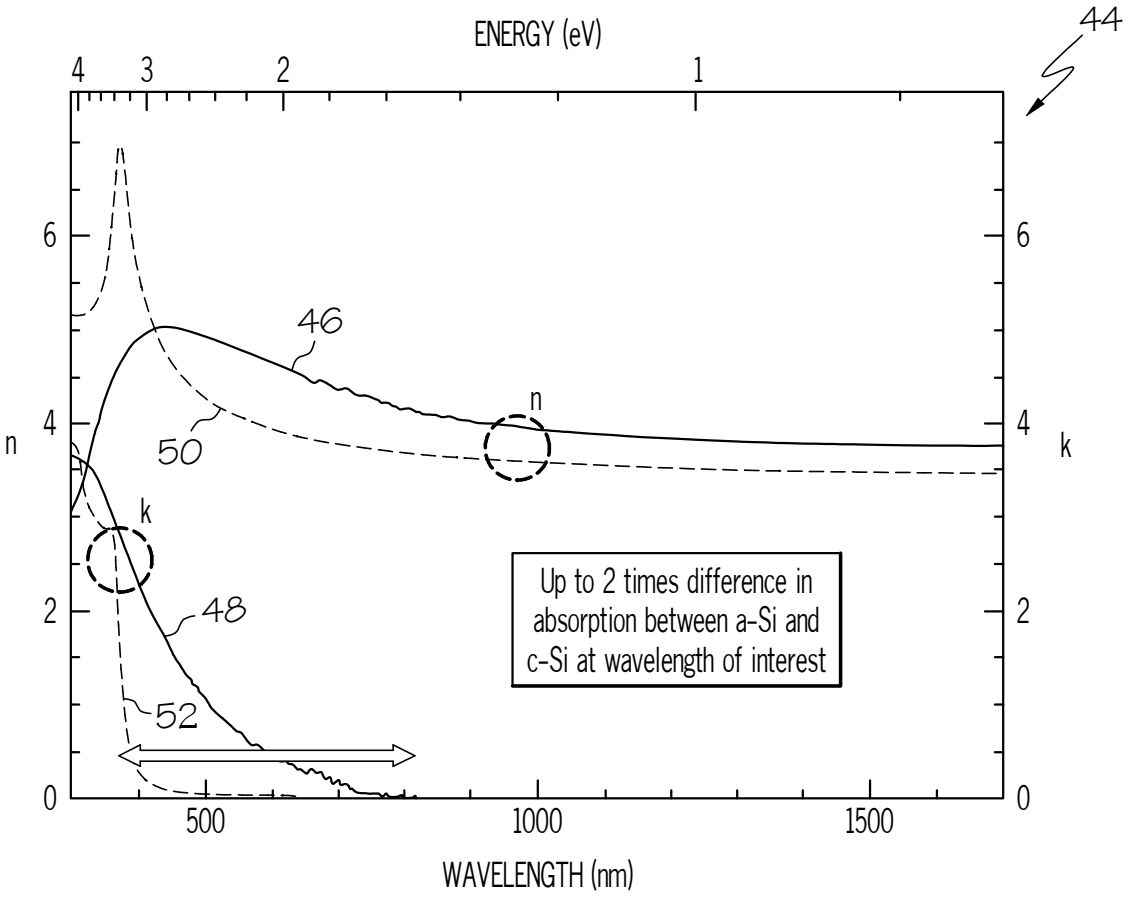

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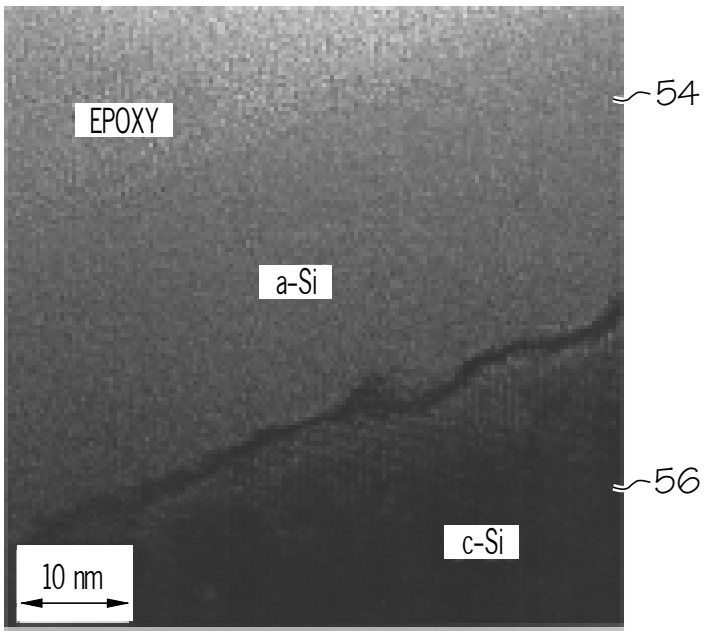

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a-Si
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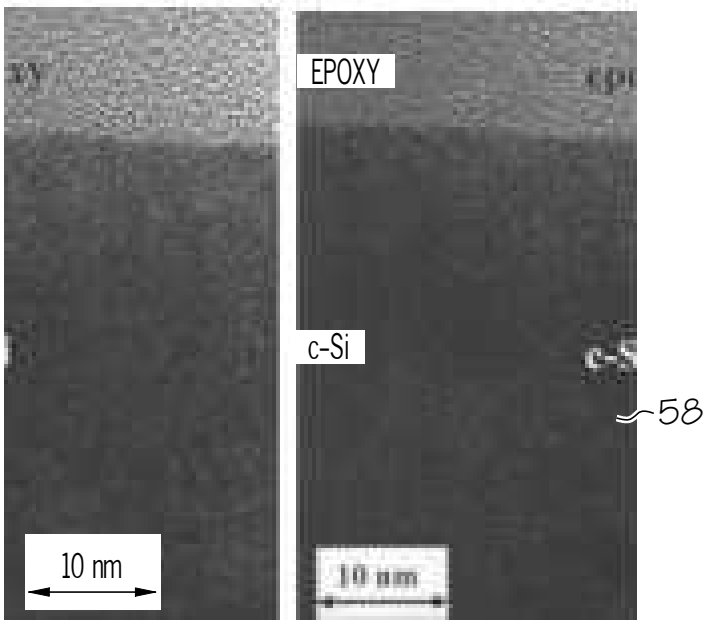

EPOXY
c-Si
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10 nm
10 nm

FIG. 9

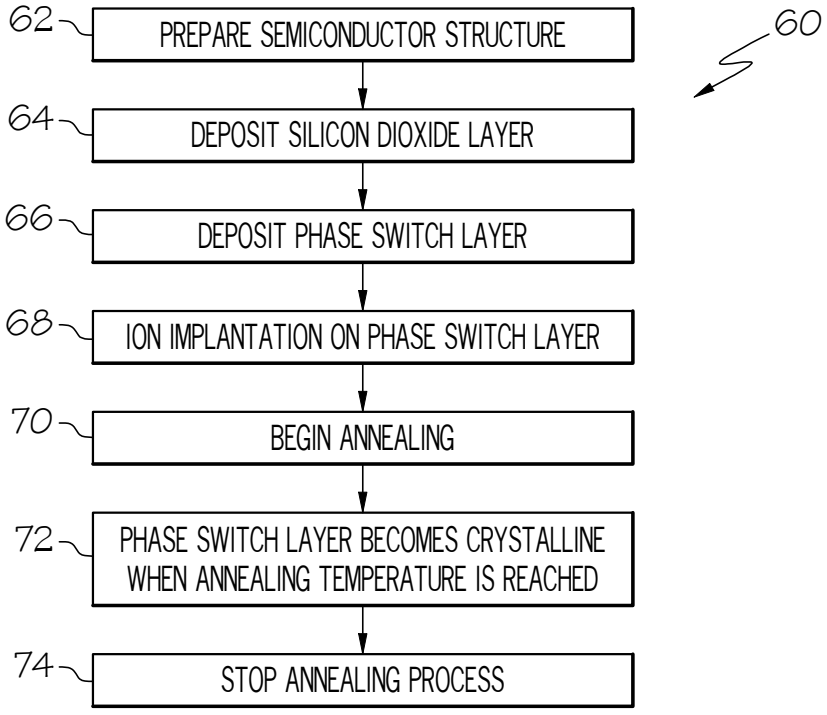

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FIG. 10